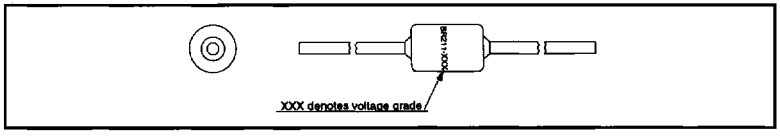
GENERAL DESCRIPTION

A range of bidirectional, breakover diodes in an axial, hermetically sealed, glass envelope. These devices feature controlled breakover voltage and high holding current together with high peak current handling capability. Typical applications include transient overvoltage protection in telecommunications equipment.

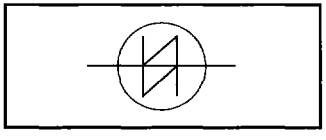
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
	BR211-100 to 280			
$V_{(BO)}$	Breakover voltage	100	280	V
I_H	Holding current	150	-	mA
I_{TSM}	Non-repetitive peak current	-	40	A

OUTLINE - SOD84



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_D	Continuous voltage		-	75% of $V_{(BO)typ}$	V
I_{TSM1}	Non repetitive peak current	10/320 µs impulse equivalent to 10/700 µs, 1.6 kV voltage impulse (CCITT K17)	-	40	A
I_{TSM2}	Non repetitive on-state current	half sine wave; t = 10 ms; T_j = 70 °C prior to surge	-	15	A
I^2t	I^2t for fusing	t_p = 10 ms	-	1.1	A^2s
dI_T/dt	Rate of rise of on-state current after $V_{(BO)}$ turn-on	t_p = 10 µs	-	50	A/µs
P_{tot}	Continuous dissipation	T_a = 25°C	-	1.2	W
P_{TM}	Peak dissipation	t_p = 1 ms; T_a = 25°C	-	50	W
T_{stg}	Storage temperature		-65	150	°C
T_a	Operating ambient temperature	off-state	-	70	°C
T_{vj}	Overload junction temperature	on-state	-	150	°C

FOR MORE DETAILED INFORMATION SEE THE LATEST ISSUE OF HANDBOOK SC02 OR DATA SHEET